

ABSTRACT OF THE DISCLOSURE

A semiconductor apparatus fabrication method is capable of effectively suppressing edge roughness when an extremely fine resist pattern is
5 formed. In the semiconductor apparatus fabrication method, the extremely fine resist pattern is covered with a film whose heat-resistance temperature is higher than the softening temperature of the resist pattern. In this state, the resist pattern is
10 heated at a temperature higher than the softening temperature and lower than the heat-resistance temperature in order to cause reflow in the resist pattern.